

April 2010

FGA20S120M 1200V, 20A ShortedAnode™ IGBT

Features

- · High speed switching
- Low saturation voltage: V_{CE(sat)} =1.55V @ I_C = 20A
- · High input impedance
- RoHS compliant

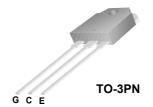
Applications

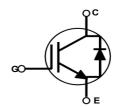
- · Induction Heating and Microwave Oven
- · Soft switching Application



General Description

Using advanced Field Stop Trench and ShortedAnode technology, Fairchild's 1200V ShortedAnode™ Trench IGBTs offer superior conduction and switching performances, and easy parallel operation with exceptional avalanche capability. This device is designed for Induction Heating and Microwave Oven.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

| Symbol | Description | | Ratings | Units |
|---------------------|---|--------------------------|-------------|-------|
| V _{CES} | Collector to Emitter Voltage | | 1200 | V |
| V _{GES} | Gate to Emitter Voltage | | ±25 | V |
| I _C | Collector Current | @ T _C = 25°C | 40 | Α |
| | Collector Current | @ T _C = 100°C | 20 | Α |
| I _{CM (1)} | Pulsed Collector Current | | 60 | А |
| I _F | Diode Continuous Forward Current | @ T _C = 25°C | 40 | А |
| I _F | Diode Continuous Forward Current | @ T _C = 100°C | 20 | А |
| P _D | Maximum Power Dissipation | @ T _C = 25°C | 348 | W |
| ' D | Maximum Power Dissipation | $@T_C = 100^{\circ}C$ | 174 | W |
| ТЈ | Operating Junction Temperature | | -55 to +175 | °C |
| T _{stg} | Storage Temperature Range | | -55 to +175 | °C |
| T _L | Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds | | 300 | °C |

Thermal Characteristics

| Symbol | Parameter | Тур. | Max. | Units |
|--|---|------|------|-------|
| $R_{\theta JC}(IGBT)$ | Thermal Resistance, Junction to Case | | 0.43 | °C/W |
| $R_{\theta JC}(Diode)$ | R _{0JC} (Diode) Thermal Resistance, Junction to Case | | 0.43 | °C/W |
| R _{θJA} Thermal Resistance, Junction to Ambient | | | 40 | °C/W |

Notes:

1: Limited by Tjmax

Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|----------------|------------|---------|-----------|------------|----------|
| FGA20S120M | FGA20S120M | TO-3PN | - | - | 30 |

Electrical Characteristics of the IGBT $T_C = 25^{\circ}C$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min. | Тур. | Max. | Units |
|----------------------|---|---|------|------|------|-------|
| Off Charac | eteristics | | | | | |
| BV _{CES} | Collector to Emitter Breakdown Voltage | V_{GE} = 0V, I_C = 2mA | 1200 | - | - | V |
| I _{CES} | Collector Cut-Off Current | $V_{CE} = V_{CES}, V_{GE} = 0V$ | - | - | 1 | mA |
| I _{GES} | G-E Leakage Current | V _{GE} = V _{GES} , V _{CE} = 0V | - | - | ±250 | nA |
| On Charac | teristics | | | 1 | | |
| V _{GE(th)} | G-E Threshold Voltage | I_C = 20mA, V_{CE} = V_{GE} | 4.5 | 6.0 | 7.5 | V |
| OL(III) | Collector to Emitter Saturation Voltage | I _C = 20A, V _{GE} = 15V T _C = 25°C | - | 1.55 | 1.85 | V |
| V _{CE(sat)} | | I _C = 20A, V _{GE} = 15V, T _C = 125°C | - | 1.75 | - | V |
| | | I _C = 20A, V _{GE} = 15V, T _C = 175°C | - | 1.85 | - | V |
| V _{FM} | Diode Forward Voltage | I _F = 20A, T _C = 25°C | | 1.7 | 2.2 | V |
| - FIVI | | I _F = 20A, T _C = 175°C | | 2.1 | - | V |
| Dynamic C | Characteristics | | | | | |
| C _{ies} | Input Capacitance | | | 2680 | | pF |
| C _{oes} | Output Capacitance | V _{CE} = 30V, V _{GE} = 0V, f = 1MHz | | 53 | | pF |
| C _{res} | Reverse Transfer Capacitance | | | 43 | | pF |
| Switching | Characcteristics | | | | | |
| t _{d(on)} | Turn-On Delay Time | | - | 43 | - | ns |
| t _r | Rise Time | | - | 176 | - | ns |
| t _{d(off)} | Turn-Off Delay Time | V _{CC} = 600V, I _C = 20A, | - | 310 | - | ns |
| t _f | Fall Time | $R_G = 10\Omega, V_{GE} = 15V,$ | - | 320 | 480 | ns |
| E _{on} | Turn-On Switching Loss | Resistive Load, T _C = 25°C | - | 0.52 | - | mJ |
| E _{off} | Turn-Off Switching Loss | | - | 1.43 | 2.15 | mJ |
| E _{ts} | Total Switching Loss | | - | 1.95 | - | mJ |
| t _{d(on)} | Turn-On Delay Time | | - | 41 | - | ns |
| t _r | Rise Time | | - | 260 | - | ns |
| t _{d(off)} | Turn-Off Delay Time | V _{CC} = 600V, I _C = 20A, | - | 345 | - | ns |
| t _f | Fall Time | $R_G = 10\Omega$, $V_{GE} = 15V$, Resistive Load, $T_C = 175^{\circ}C$ | - | 520 | - | ns |
| E _{on} | Turn-On Switching Loss | | - | 0.78 | - | mJ |
| E _{off} | Turn-Off Switching Loss | | - | 1.97 | - | mJ |
| E _{ts} | Total Switching Loss | | - | 2.75 | - | mJ |
| Q _g | Total Gate Charge | | - | 208 | - | nC |
| Q _{ge} | Gate to Emitter Charge | $V_{CE} = 600V, I_{C} = 20A,$ | - | 18 | - | nC |
| Q _{gc} | Gate to Collector Charge | V _{GE} = 15V | - | 119 | - | nC |

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

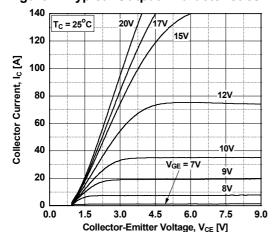


Figure 3. Typical Saturation Voltage Characteristics

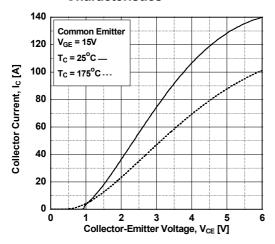


Figure 5. Saturation Voltage vs. Case
Temperature at Variant Current Level

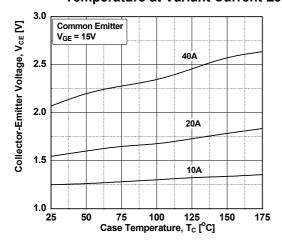


Figure 2. Typical Output Characteristics

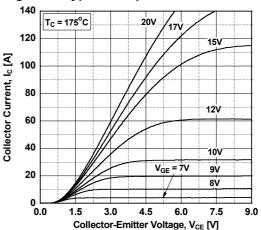


Figure 4. Transfer Characteristics

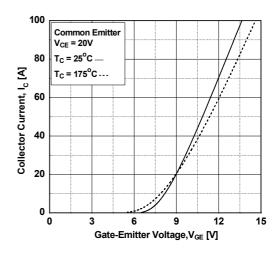
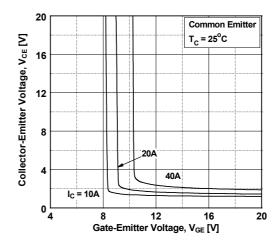


Figure 6. Saturation Voltage vs. Vge



Typical Performance Characteristics

Figure 7. Saturation Voltage vs. V_{GE}

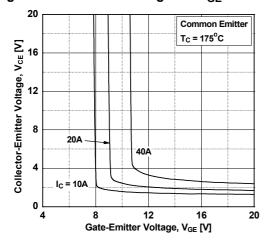


Figure 9. Gate Charge Characteristics

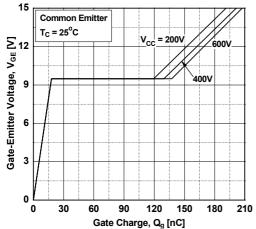


Figure 11. Turn-On Characteristics vs.
Gate Resistance

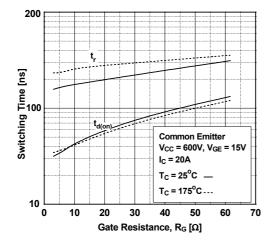


Figure 8. Capacitance Characteristics

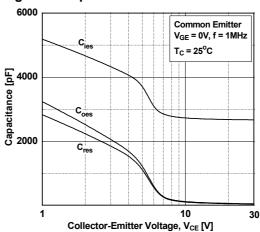


Figure 10. SOA Characteristics

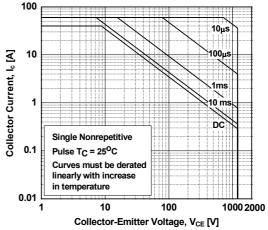
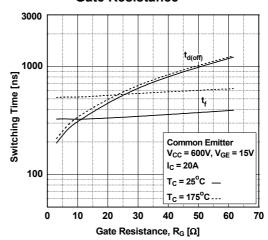


Figure 12. Turn-Off Characteristics vs.
Gate Resistance



Typical Performance Characteristics

Figure 13. Turn-On Characteristics vs. Collector Current

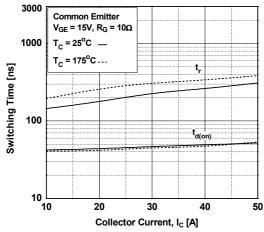


Figure 15. Switching Loss vs.

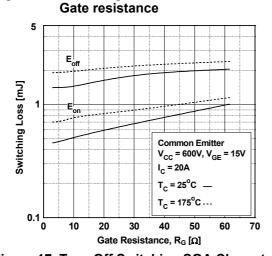


Figure 17. Turn-Off Switching SOA Characteristics Collector Currrent

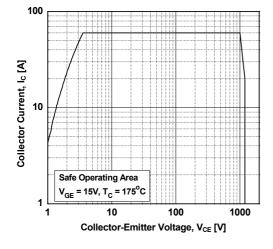


Figure 14. Turn-off Characteristics vs.
Collector Current

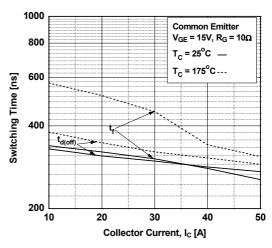


Figure 16. Switching Loss vs. Collector Current

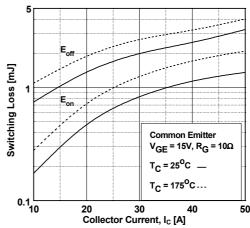
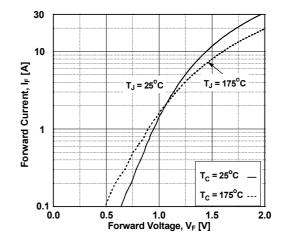
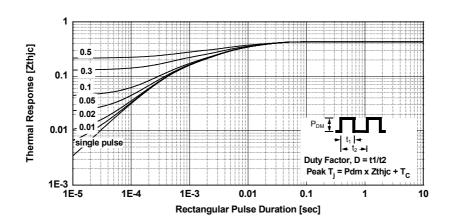


Figure 18. Diode Forward Characteristics







Mechanical Dimensions TO-3PN 5.00 4.60 ø3.30 3.10 15,80 15.40 1.65 1.45 (R0.50) 20.10 19,70 18.90 18.50 (1.85)2.20 1.80 3 20 2 80 20.30 19.70 **⊕** Ø0.55**⋈** 1.20 0.80 3 1 5.45 5.45 (R0.50) Dimensions in Millimeters



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